



**NB013,014 (NPN) 30mA low noise transistors
NB023,024 (PNP)**

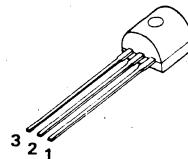
features

- 35 to 50 Volt at 30mA collector ratings
- 300mV guaranteed V_{CE} (sat) characteristics at $I_C = 10\text{mA}$ and $I_B = 0.5\text{mA}$
- 1dB typical wide-band Noise Figure
- "Epoxy B" packaging concept for excellent reliability

applications

- Low noise amplifier circuits
- Equalizer, preamplifiers

1 package and lead coding

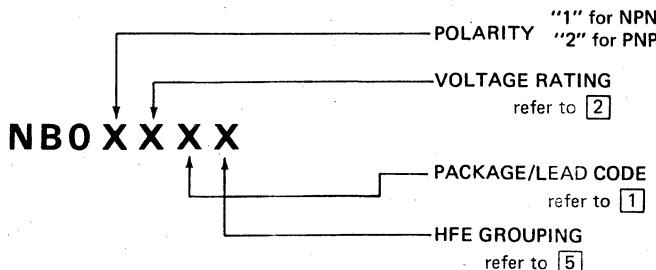


PACKAGE CODE TO-92	LEAD		
	1	2	3
E	E	B	C
F	E	C	B
H	C	B	E

2 maximum ratings

PARAMETER	SYMBOL	NB013 NB023	NB014 NB024	UNIT
Collector-Emitter Voltage	V_{CEO}	35	50	V_{DC}
Collector-Base Voltage	V_{CB}	40	55	V_{DC}
Emitter-Base Voltage	V_{EB}	5	5	V_{DC}
Collector Current (continuous)	I_C (max)	30	30	mA_{DC}
Power Dissipation ($T_A = 25^\circ\text{C}$)	P_D	0.6	0.6	W
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	1.0	1.0	W
Thermal Resistance	θ_{JA}	208	208	$^\circ\text{C}/\text{W}$
	θ_{JC}	125	125	$^\circ\text{C}/\text{W}$
Temperature, Junction and Storage	T_J, T_{stg}	-55 to + 150	-55 to + 150	$^\circ\text{C}$

3 ordering information

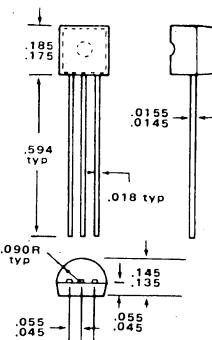
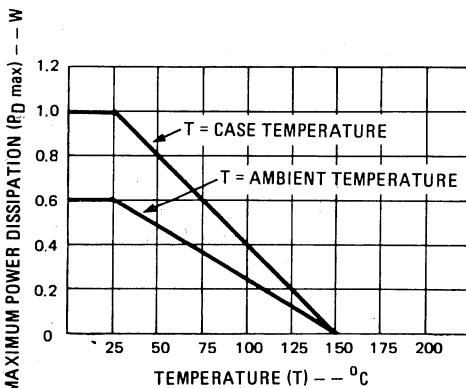


4 electrical characteristics $T_C = 25^\circ\text{C}$

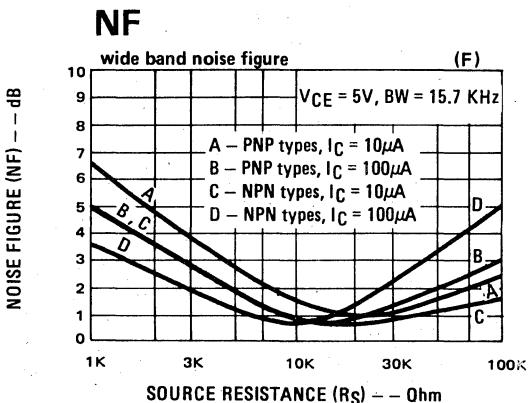
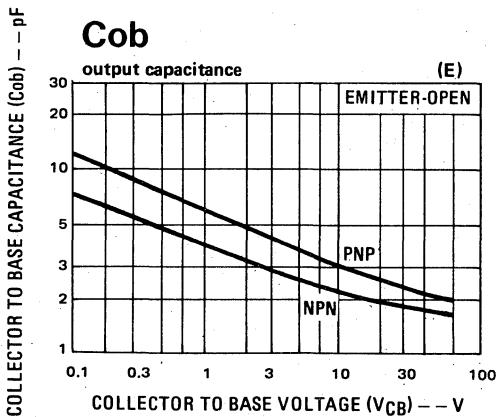
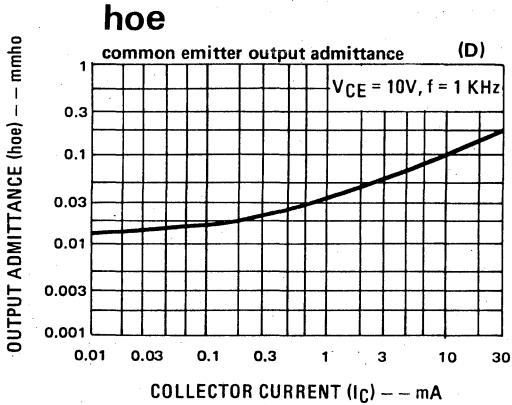
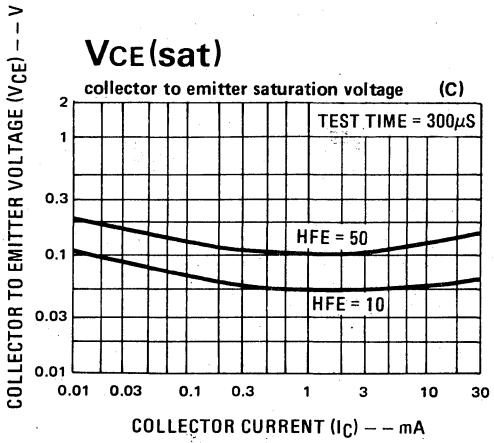
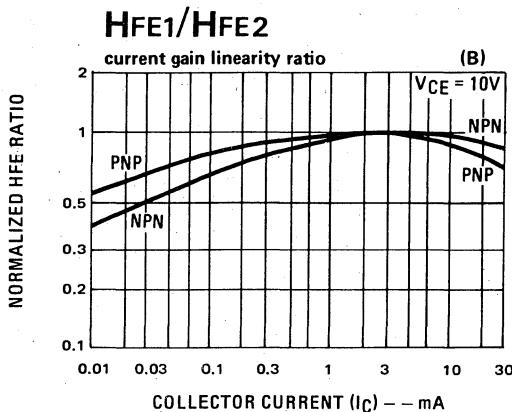
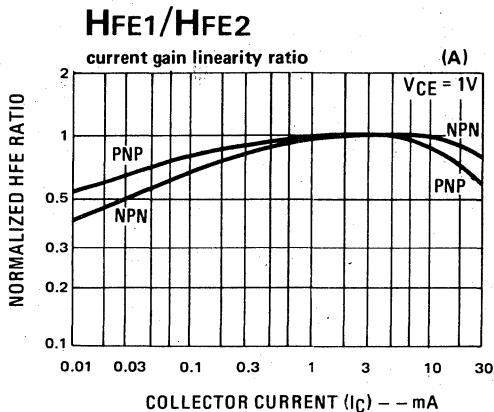
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{CEO}	Collector-Emitter Sustaining Voltage NB013/023 NB014/024	$I_C = 1 \text{ mA}$	35			V
			50			V
BV_{CBO}	Collector-Base Breakdown Voltage NB013/023 NB014/024	$I_C = 100 \mu\text{A}$	40			V
			55			V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu\text{A}$	5			V
I_{CEO}	Collector-Emitter Leakage Current	$V_{\text{CE}} = 30\text{V}$ NB013 45V NB014		1	1	μA
I_{CES}	Collector-Emitter Leakage Current	$V_{\text{CE}} = 30\text{V}$ NB023 45V NB024		0.5	0.5	μA
I_{CBO}	Collector-Base Leakage Current	$V_{\text{CB}} = 35\text{V}$ NB013/023 50V NB014/024		50	50	nA
I_{EBO}	Emitter-Base Leakage Current	$V_{\text{EB}} = 4\text{V}$		0.1		μA
$V_{\text{BE}}(\text{sat})$	Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$	0.75	0.95		V
$V_{\text{CE}}(\text{sat})$	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$	0.1	0.3		V
C_{ob}	Collector Output Capacitance NPN types PNP types	$V_{\text{CB}} = 10\text{V}, f = 1 \text{ MHz}$	2	3		pF
f_t	Current Gain Bandwidth Product	$I_C = 1 \text{ mA}, V_{\text{CE}} = 5\text{V}$	50	120		MHz
NF	Noise Figure	$I_C = 10 \mu\text{A}, V_{\text{CE}} = 5\text{V}$ $R_S = 10 \text{ K}, \text{BW} = 15.7 \text{ KHz}$		1	4	dB

5 HFE groupings

GROUPING	PARAMETER	CONDITIONS	MIN	TYP	MAX	RATIO
I	DC Current Gain	$I_C = 100 \mu\text{A}, V_{\text{CE}} = 5\text{V}$	140	180	240	1:1.6
J	DC Current Gain	$I_C = 100 \mu\text{A}, V_{\text{CE}} = 5\text{V}$	200	260	350	1:1.6
K	DC Current Gain	$I_C = 100 \mu\text{A}, V_{\text{CE}} = 5\text{V}$	300	380	500	1:1.6
L	DC Current Gain	$I_C = 100 \mu\text{A}, V_{\text{CE}} = 5\text{V}$	450	580	750	1:1.6
T	DC Current Gain	$I_C = 100 \mu\text{A}, V_{\text{CE}} = 5\text{V}$	100	150	240	1:2.4
U	DC Current Gain	$I_C = 100 \mu\text{A}, V_{\text{CE}} = 5\text{V}$	200	320	500	1:2.4
V	DC Current Gain	$I_C = 100 \mu\text{A}, V_{\text{CE}} = 5\text{V}$	450	700	1100	1:2.4
Y	DC Current Gain	$I_C = 100 \mu\text{A}, V_{\text{CE}} = 5\text{V}$	100	190	350	1:3.5
Z	DC Current Gain	$I_C = 100 \mu\text{A}, V_{\text{CE}} = 5\text{V}$	300	580	1100	1:3.5

6 physical dimensions

7 max power dissipation


8 typical performance characteristics



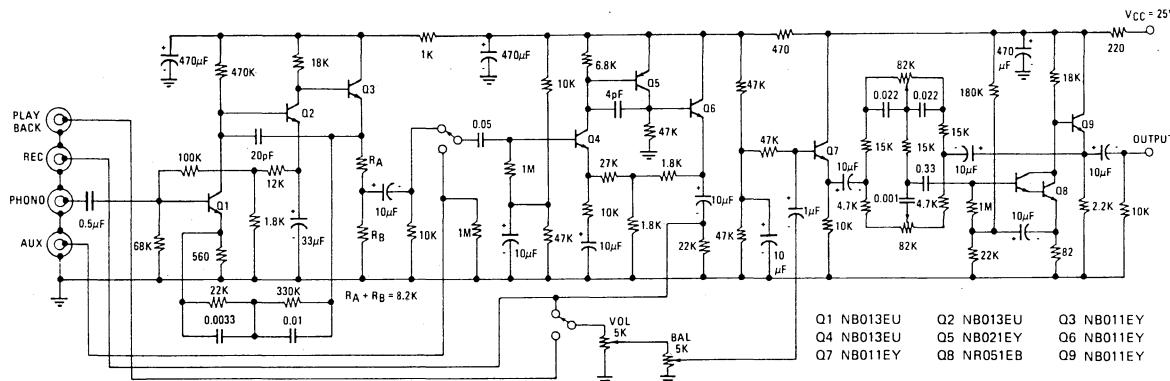


Figure A. High Quality Preamplifier with Tone Control Circuit

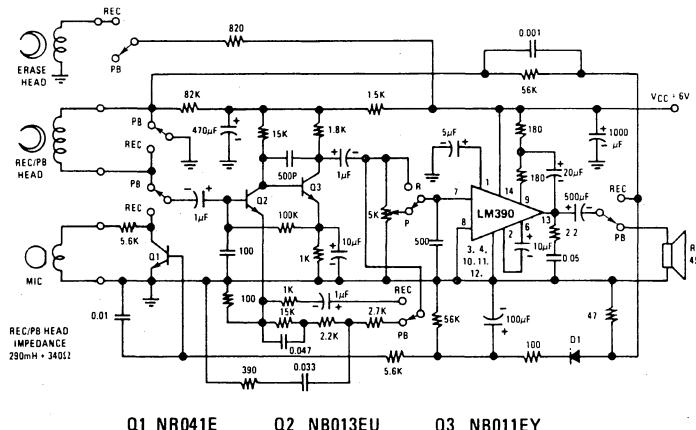


Figure B. Battery Operated Recording/Playback Cassette Circuit

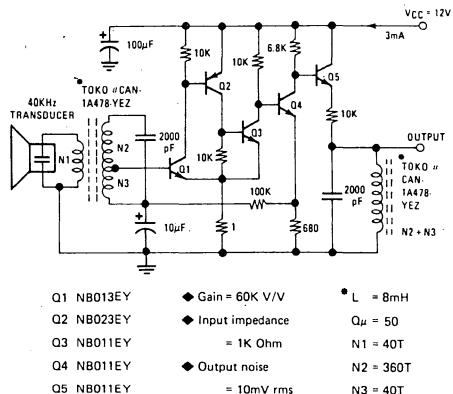


Figure C. High Gain Ultrasonic Amplifier